

Descriptions

- Switching application
- Interface circuit and driver circuit application

Features

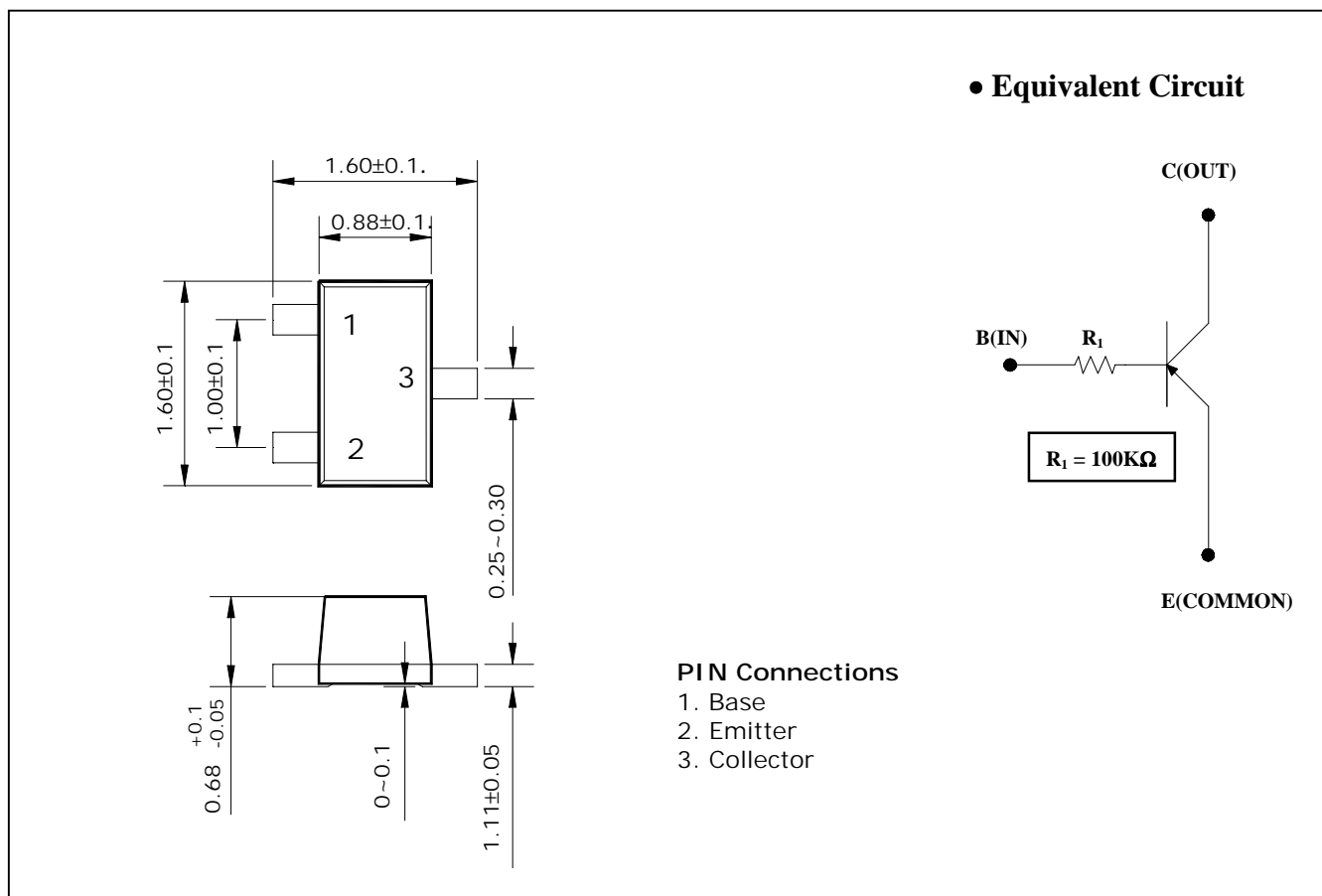
- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process
- High packing density

Ordering Information

Type NO.	Marking	Package Code
SRA2212EF	BR	SOT-523F

Outline Dimensions

unit : mm



Absolute maximum ratings

(Ta=25°C)

Characteristic	Symbol	Ratings	Unit
Collector-Base Voltage	V _{CBO}	-50	V
Collector-Emitter Voltage	V _{CEO}	-50	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current	I _C	-100	mA
Power Dissipation	P _D	150	mW
Junction Temperature	T _J	150	°C
Storage Temperature	T _{STG}	-55 ~ 150	°C

Electrical Characteristics

(Ta=25°C)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector Cut-off Current	I _{CBO}	V _{CB} =-50V, I _E =0	-	-	-500	nA
Emitter Cut-off Current	I _{EBO}	V _{EB} =-5V, I _C =0	-	-	-500	nA
DC Current Gain	h _{FE}	V _{CE} =-5V, I _C =-1mA	120	-	-	-
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	I _C =-10mA, I _B =-0.5mA	-	-0.1	-0.3	V
Transition Frequency	f _T *	V _{CE} =-10V, I _C =-5mA	-	250	-	MHz
Input Resistance	R ₁	-	-	100	-	KΩ

* : Characteristic of Transistor Only

Electrical Characteristic Curves

Fig. 1 h_{FE} - I_C

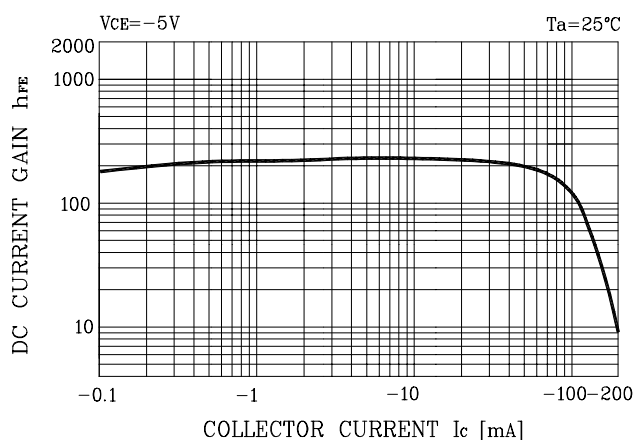


Fig. 2 V_{CE(SAT)} - I_C

